

isc Silicon PNP Power Transistor

MJD350

DESCRIPTION

- Collector–Emitter Sustaining Voltage–  
:  $V_{CEO(SUS)} = -300\text{ V(Min)}$
- Low Collector Saturation Voltage–  
:  $V_{CE(sat)} = -1.0\text{V(Max.)}@ I_C = -50\text{mA}$
- DPAK for Surface Mount Applications
- Complement to Type MJD340
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

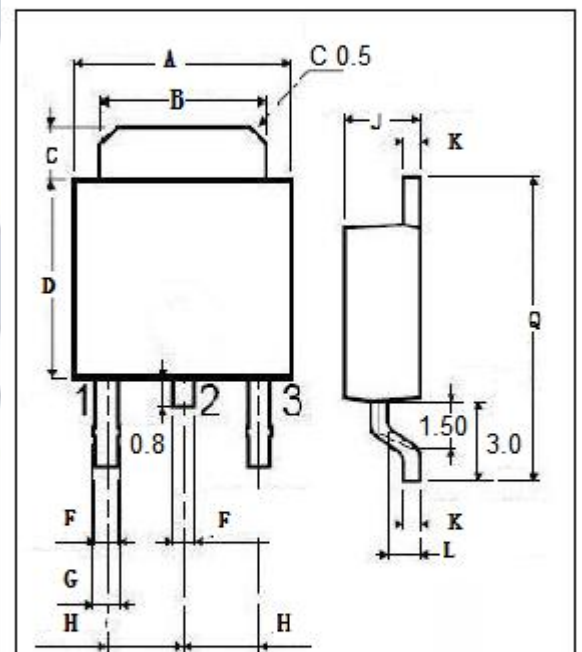
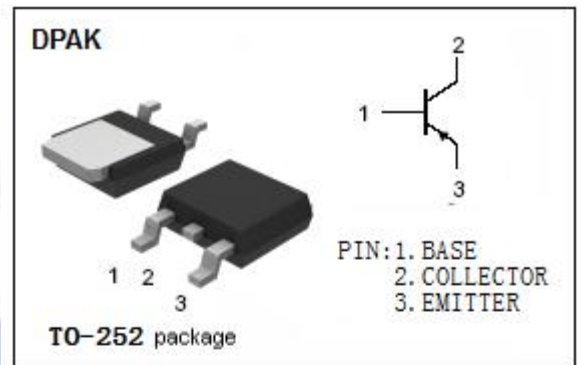
- Designed for line operated audio output amplifier, switchmode power supply drivers and other switching applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-300	V
$V_{CEO}$	Collector-Emitter Voltage	-300	V
$V_{EBO}$	Emitter-Base Voltage	-3	V
$I_C$	Collector Current-Continuous	-0.5	A
$I_{CM}$	Collector Current-Peak	-0.75	A
$P_C$	Collector Power Dissipation $T_c=25^\circ\text{C}$	15	W
	Collector Power Dissipation $T_a=25^\circ\text{C}$	1.56	
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	8.33	$^\circ\text{C/W}$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	80	$^\circ\text{C/W}$



DIM	mm	
	MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

**isc Silicon PNP Power Transistor****MJD350****ELECTRICAL CHARACTERISTICS** $T_c = 25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = -1.0\text{mA}; I_B = 0$	-300		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -1.0\text{mA}; I_E = 0$	-300		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -1.0\text{mA}; I_C = 0$	-3		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -50\text{mA}; I_B = -5\text{mA}$		-1.0	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -300\text{V}; I_E = 0$		-0.1	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -3\text{V}; I_C = 0$		-0.1	mA
$h_{FE}$	DC Current Gain	$I_C = -50\text{mA}; V_{CE} = -10\text{V}$	30	240	